

**isc Silicon PNP Power Transistor**

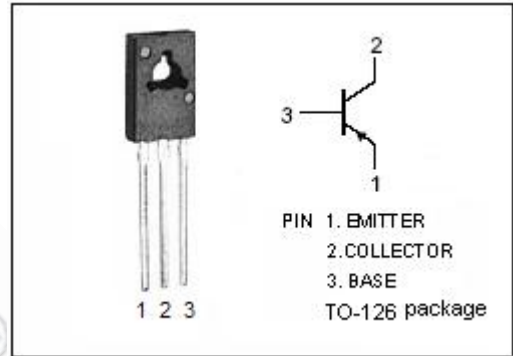
**2SA1360**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -150V$  (Min)
- Complement to Type 2SC3423

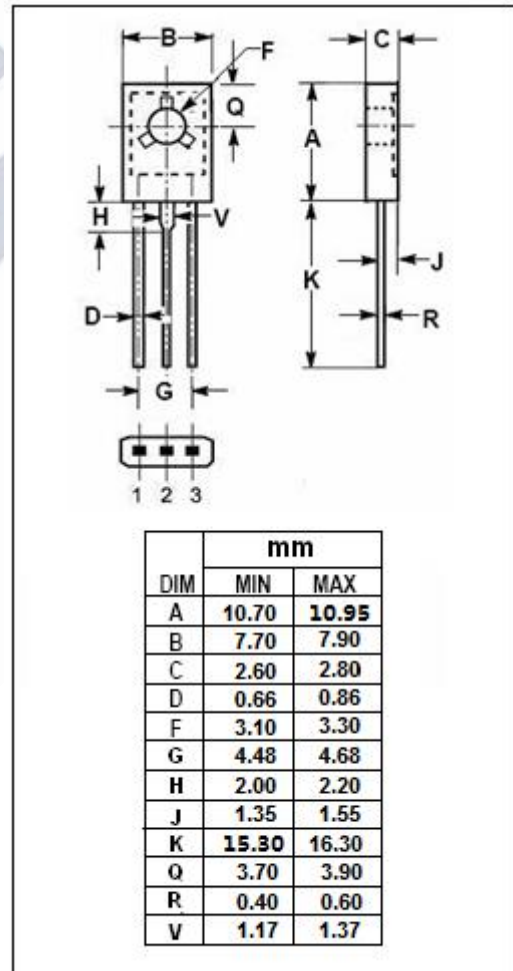
**APPLICATIONS**

- Designed for audio frequency amplifier applications.



**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-150	V
$V_{CEO}$	Collector-Emitter Voltage	-150	V
$V_{EBO}$	Emitter-Base Voltage	-5.0	V
$I_C$	Collector Current-Continuous	-50	mA
$I_B$	Base Current-Continuous	-5	mA
$P_C$	Collector Power Dissipation @ $T_a=25^\circ C$	1.2	W
	Total Power Dissipation @ $T_C=25^\circ C$	5	
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



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**2SA1360**
**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>B</sub> = 0	-150			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10mA; I <sub>B</sub> = -1mA			-1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -10mA; V <sub>CE</sub> = -5V			-0.8	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -150V; I <sub>E</sub> = 0			-0.1	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-0.1	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -10mA; V <sub>CE</sub> = -5V	80		240	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -10mA; V <sub>CE</sub> = -10V		100		MHz

**◆ h<sub>FE</sub> Classifications**

O	Y
80-160	120-240